USPTO Form 1449 Serial No. Attorney Docket No. Patent and Trademark Office 2846/2112 10/660,348 INFORMATION DISCLOSURE STATEMENT Applicant(s): Ren et al. Filing Date: Setpember 11, 2003 Group: 1775 **U.S. PATENT DOCUMENTS** Examiner Patent No. Date Name Class Subclas Filing Date Initial (if appropriate) S 6,855,202 February 15, 2005 Alivisatos et al. 117 68 November 20, 2002 6,863,943 March 8, 2005 Wang et al. 428 37 January 13, 2004 FOREIGN PATENT DOCUMENTS Examiner Document No. **Publication** Class Subclas Country Translation Initial Date S YES NO OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.) International Search Report based on PCT/US03/28530 dated April 7, 2005. DATE CONSIDERED **EXAMINER** (0/13/05 *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant. **Copies of references not provided at the time of this submission.

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